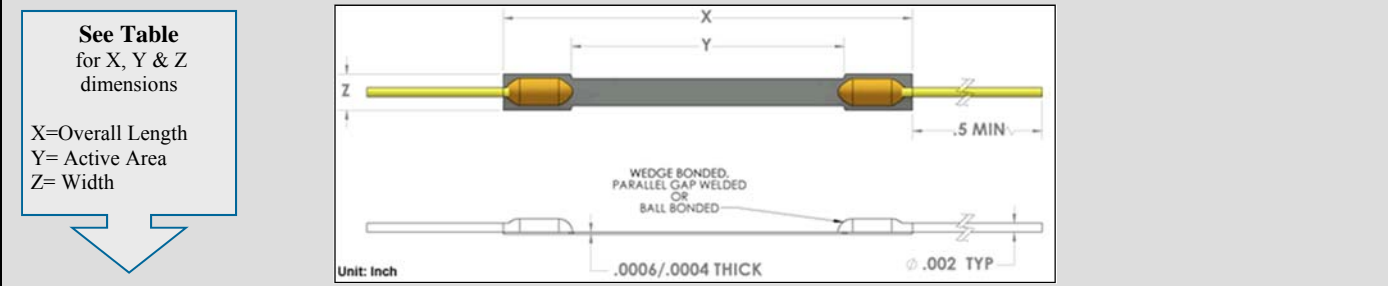


BAR STRAIN GAGE DATA

BAR GAGE SCHEMATIC

BAR SEMICONDUCTOR STRAIN GAGES

Part Number X Y	Z	Lead Attachment	Thickness	Resistance Ohms @ 78°F	Gage Factor	TCGF	TCR
SS-027-013-500P	.009	Ball Bond	.0004	540±50	155±10	-18%	24%
SS-037-022-500P	.009	Ball Bond	.0004	540±50	150±10	-13%	17%
SS-060-033-500P	.008	Welded	.0004	540±50	140±10	-13%	15%
SS-060-033-750P	.008	Welded	.0004	750±90	145±10	-15%	18%
SS-060-033-1000P	.008	Welded	.0004	1050±75	155±10	-18%	24%
SS-080-050-120P	.008	Welded	.0004	120±20	120±10	-9%	5%
SS-080-050-230P	.008	Welded	.0004	230±30	120±10	-9%	5%
SS-080-050-345P	.008	Welded	.0004	345±40	140±10	-13%	16%
SS-080-050-500P	.008	Welded	.0004	540±50	140±10	-13%	16%
SS-080-050-500P	.008	Ball Bond	.0004	540±50	140±10	-13%	16%
SS-080-050-1000P	.008	Welded	.0004	1050±75	155±10	-18%	24%
SS-090-060-500P	.008	Welded	.0004	540±50	140±10	-13%	16%
SS-090-060-1150P	.008	Welded	.0004	1125±75	155±10	-18%	24%
SS-150-124-15P	.008	Welded	.0010	15±2	100±10	-10%	6%
SS-150-124-25P	.008	Welded	.0009	25±3	100±10	-10%	6%
SS-150-124-30P	.008	Welded	.0008	30±3	100±10	-10%	6%
SS-150-124-40P	.008	Welded	.0007	40±4	100±10	-10%	6%
SS-250-225-120P	.009	Welded	.0004	120±20	100±10	-10%	6%

STRAIN GAGE ORDERING INFO

STANDARD SEMICONDUCTOR STRAIN GAGES

Micron semiconductor strain gages are made from "P" doped bulk silicon. This is a two terminal resistive device. The silicon is micro machined to shape thus eliminating molecular dislocation or cracks, thereby optimizing performance.

STANDARD GAGE SPECIFICATIONS

Materials	Czochralski pulled boron doped silicon
Leads	.002 dia. Gold x 0.5 in. long. Some gages have .0015 dia. Leads.
Contact Pads	Gold nickel fused, vapor deposited gold or vapor deposited aluminum for Hi-Temp
Lead Attachments	Parallel gap welded with epoxy reinforcement. Ball Bond or Wedge Bond
Operating Strain	±2000 μ inch/inch (3000 μ inch/inch max.)
Linearity	Better than ±0.25% to 600 μ inch/inch Better than ±1.5% to 1500 μ inch/inch
Max. Operating Temperature	500°F

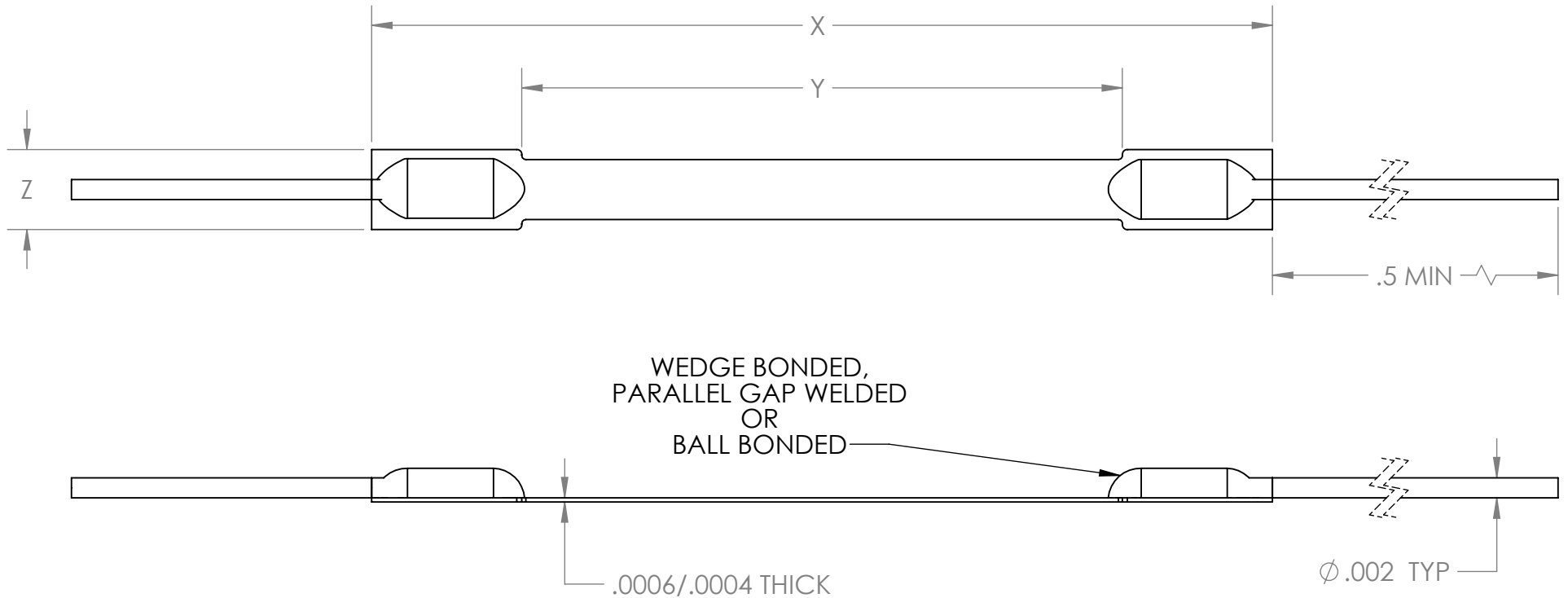
Ordering Guidelines	Example
A. Model (SS)	<p>SS-080-050-500P U S4 is a Semiconductor Strain gage with a total length of 080 and an active length of 050. The gage has a nominal resistance of 500 at 78 degrees F. The gage is further defined as Dopant P and Configured as a 'U'* Gage. S4 specifies a matched set of 4 gages.</p> <p>Note:</p> <ul style="list-style-type: none"> ▪ S4 Matched set of 4 gages ▪ S2 Matched set of 2 gages. ▪ S1 Single gage with data. ▪ S0 Bulk gage without data. <p>*Specify Gage Type: "U", "M" or Leave Blank for Bar Gage. For Matched Sets of S5 up to sets of S16 Consult Factory</p>
B. Total Length	
C. Active Length	
D. Nominal Resistance at 78°F	
E. Dopant	
F. U Gage , M Gage, or Leave Blank for Bar Gage*	
G. Specifies Single, Matched or Bulk Gages	

Standard Bridge Matching

Temperature °F	0°	78°	278°	
Standard Matching	±0.6%	±0.4%	±0.4%	Percent of Base Resistance

Note: Custom special matching gages (Mil-Spec.) or additional data points are also available.

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		UNLESS OTHERWISE SPECIFIED:		NAME	DATE
		DIMENSIONS ARE IN INCHES		DRAWN	x
		TOLERANCES:		CHECKED	09/09/13
		ANGULAR: MACH ± 0° 30		ENG APPR.	
		ONE PLACE DECIMAL ± .030		MFG APPR.	
		TWO PLACE DECIMAL ± .010		Q.A.	
		THREE PLACE DECIMAL ± .005		COMPANY:	
		ALL DIA .005 TIR, RADII .005 MAX			
		SURFACE FINISH $\sqrt{32}$			
		INTERPRET GEOMETRIC TOLERANCING PER:			
		MATERIAL			
		FINISH			
	NEXT ASSY	USED ON			
	APPLICATION				

MICRON INSTRUMENTS

TITLE:

BAR GAGE

SIZE A	DWG. NO. MI-WEB	REV -
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SCALE: 64:1 WEIGHT: SHEET 1 OF 1